

Plastic Infrared Light Emitting Diode

OED234

Description

The QED234 is a 940 nm GaAs / AlGaAs LED encapsulated in a clear untinted, plastic T-1 3/4 package.

Features

- $\lambda = 940 \text{ nm}$
- Chip Material = GaAs with AlGaAs Window
- Package Type: T-1 3/4 (5 mm lens diameter)
- Matched Photosensor: QSD123/124
- Medium Emission Angle, 40°
- High Output Power
- Package Material and Color: Clear, Untinted, Plastic
- Ideal for Remote Control Applications
- This is a Pb-Free Device

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
T _{OPR}	Operating Temperature	40 to +100	°C	
T _{STG}	Storage Temperature	40 to +100	°C'Sold (Flow (Note	')

		260 for 10 s	°C
I _F	Continuous Forward Current	100	mA
V _R	Reverse Voltage	5	V
P _D	Power Dissipation (Note 1)	200	mW
I _{FP}	Peak Forward Current	1.5	Α

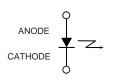
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Derate power dissipation linearly 2.67 mW/°C above 25°C.
- 2. RMA flux is recommended.
- 3. Methanol or Isopropyl alcohols are recommended as cleaning agents.
- 4. Soldering iron 1/16" (1.6 mm) minimum from housing.
- 5. Pulse conditions; tp = 100 μ s, T = 10 ms



T-1 3/4, 5MM LED CASE 100CC

CONNECTION DIAGRAM



ORDERING INFORMATION

Tem pevalce re	Package	Shipping [†]
QED234	T 1 3/4,5MM LED (Pb Free)	250 / Bulk Bag

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

(Note 3)

QED234

ELECTRICAL / OPTICAL CHARACTERISTICS

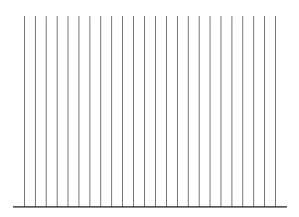
Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

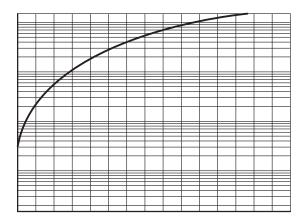
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
λ_{PE}	Peak Emission Wavelength	I _F = 20 mA		940		nm
	Spectral Bandwidth	I _F = 20 mA	50			nm
TC_{λ}	Temp. Coefficient of λ_{PE}	I _F = 100 mA		0.2		nm/K
2Θ _{1/2}	Emission Angle	I _F = 100 mA		40		0
V _F	Forward Voltage	$I_F = 100 \text{ mA}, \text{ tp} = 20 \text{ ms}$			1.6	V
TC_v	Temp. Coefficient of V _F	I _F = 100 mA		1.5		mV/K
I _R	Reverse Current	V _R = 5 V			10	ns
ΙE	Radiant Intensity	$I_F = 100 \text{ mA}, \text{ tp} = 20 \text{ ms}$	27			ns
TCI	Temp. Coefficient of I _E	I _F = 20 mA		0.6		ns
t _r	Rise Time	I _F = 100 mA		1000		ns
t _f	Fall Time			1000		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

QED234

TYPICAL CHARACTERISTICS





T-1 3/4, 5MM LED CASE 100CC ISSUE O

DATE 30 NOV 2016

Notes:

1. Dimensions f

